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Siliup Semiconductor

SP60N13GDNK

60V N-Channel Power MOSFET

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}TYP$	$I_D$
60V	13mΩ@10V	25A
	16mΩ@4.5V	

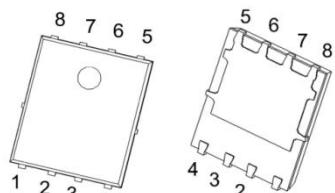
## Feature

- Fast switching speed
- Surface mount package
- Reliable and Rugged
- ROHS Compliant & Halogen-Free

## Applications

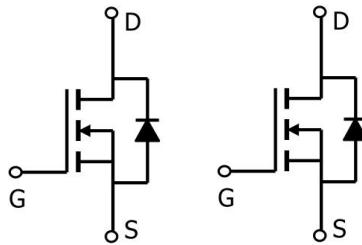
- DC-DC Converters.
- Motor Control.

## Package

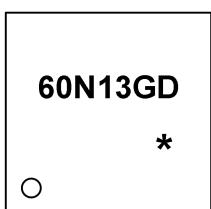


PDFNWB5X6-8L

## Circuit diagram



## Marking



60N13GD

\*

=Device Code

=Month Code



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**Absolute maximum ratings (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current(Tc=25°C)	I <sub>D</sub>	25	A
Pulse Drain Current Tested	I <sub>DM</sub>	100	A
Maximum Power Dissipation(Tc=25°C)	P <sub>D</sub>	73	W
Thermal Resistance-Junction to Case	R <sub>θJC</sub>	1.71	°C/W
Maximum Junction Temperature	T <sub>J</sub>	-55 to 150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to 150	°C

**Electrical characteristics (Ta=25°C, unless otherwise noted)**

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static Electrical Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, ID=250mA	60	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1	uA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , ID=250uA	1.0	1.8	2.5	V
Drain-Source On-state Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, ID=10A	-	13	16	mΩ
		V <sub>GS</sub> =4.5V, ID=10A	-	16	21	
<b>Dynamic and Switching Characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =30V, F=1MHz	-	426	-	pF
Output Capacitance	C <sub>oss</sub>		-	103	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	8	-	
Turn-on Delay Time	t <sub>d(ON)</sub>	VDD=30V, ID=10A, VGS=10V, R <sub>G</sub> =1.6Ω	-	8	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	5	-	
Turn-off Delay Time	t <sub>d(OFF)</sub>		-	24	-	
Turn-off Fall Time	t <sub>f</sub>		-	3.5	-	
Total Gate Charge	Q <sub>g</sub>	VDS=30V, VGS=10V, ID=10A	-	35	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	6.4	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	3.5	-	
<b>Source-Drain Characteristics</b>						
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	-	1.2	V



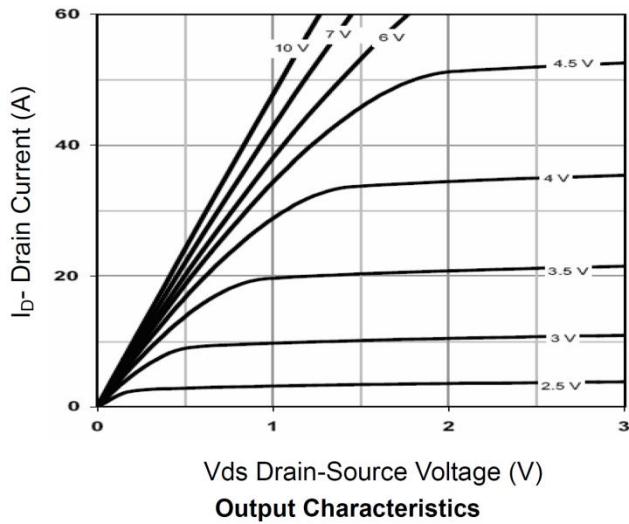
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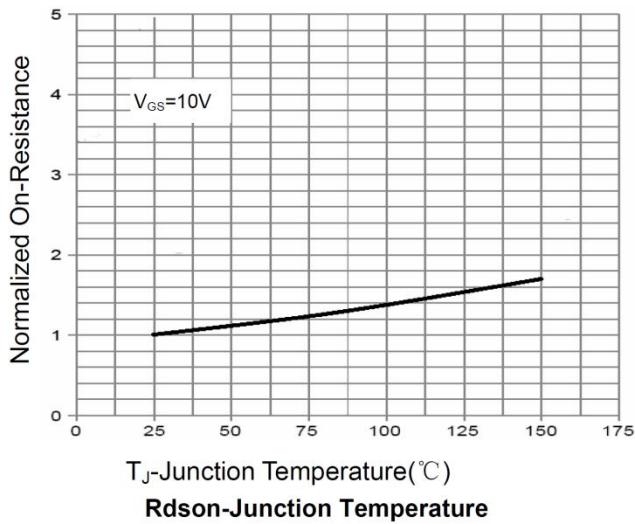
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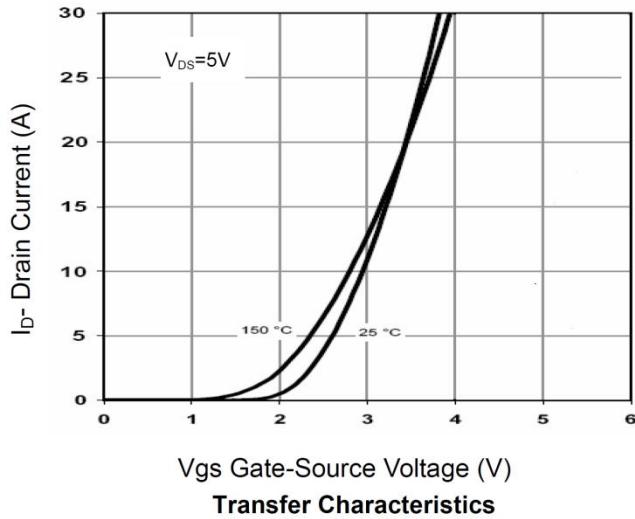
## Typical Characteristics



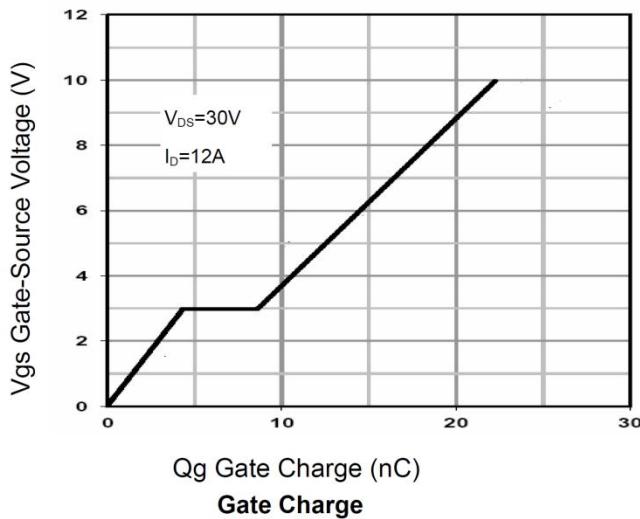
Output Characteristics



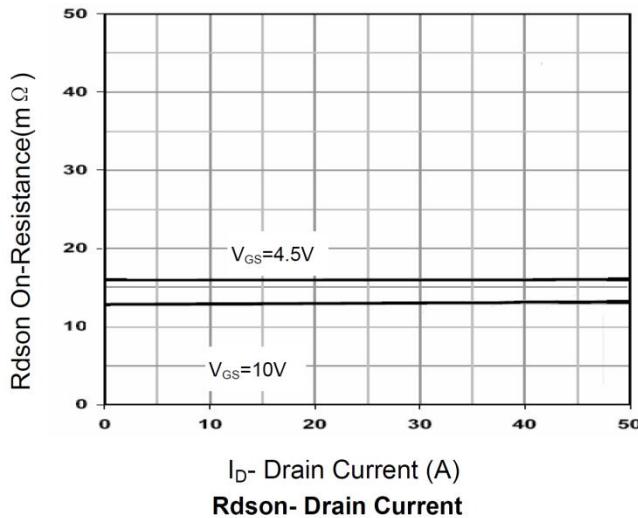
R<sub>dson</sub>-Junction Temperature



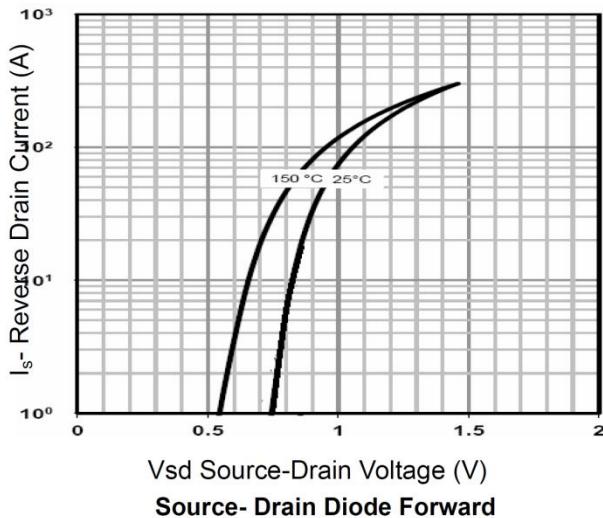
Transfer Characteristics



Gate Charge



R<sub>dson</sub>- Drain Current



Source- Drain Diode Forward

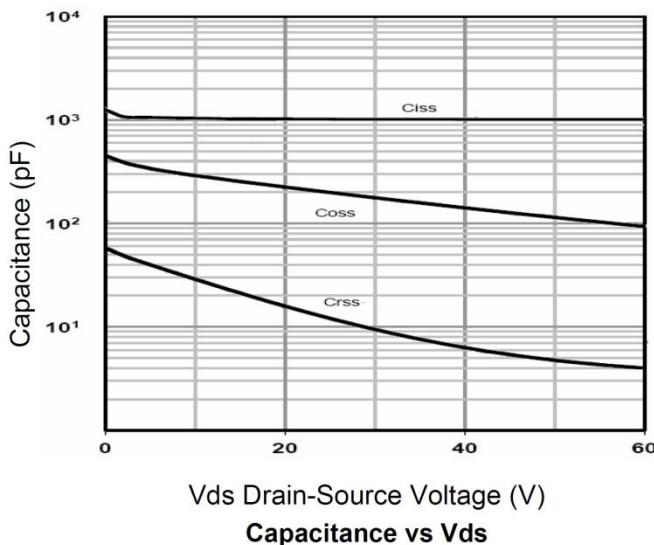


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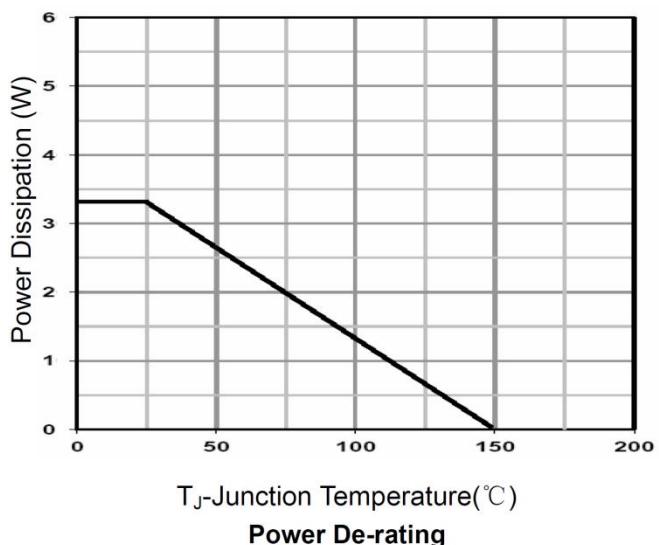
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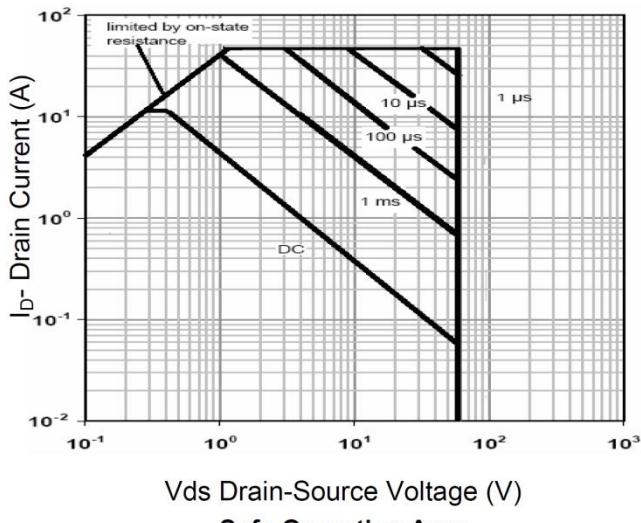
60V N-Channel Power MOSFET



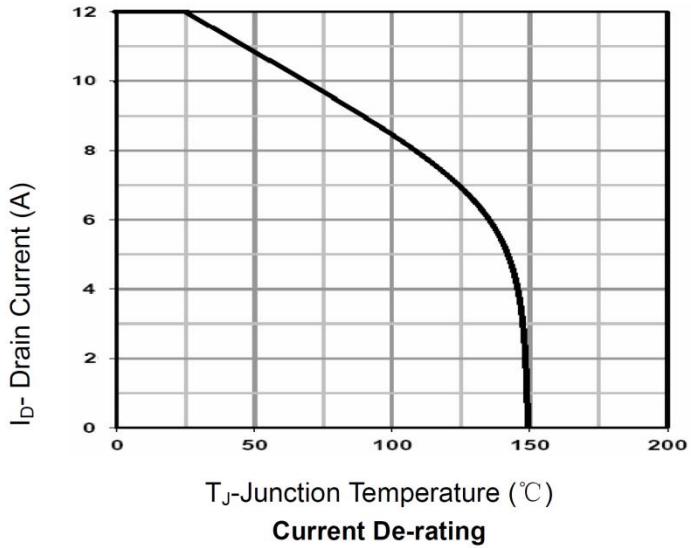
V<sub>DS</sub> Drain-Source Voltage (V)  
Capacitance vs V<sub>DS</sub>



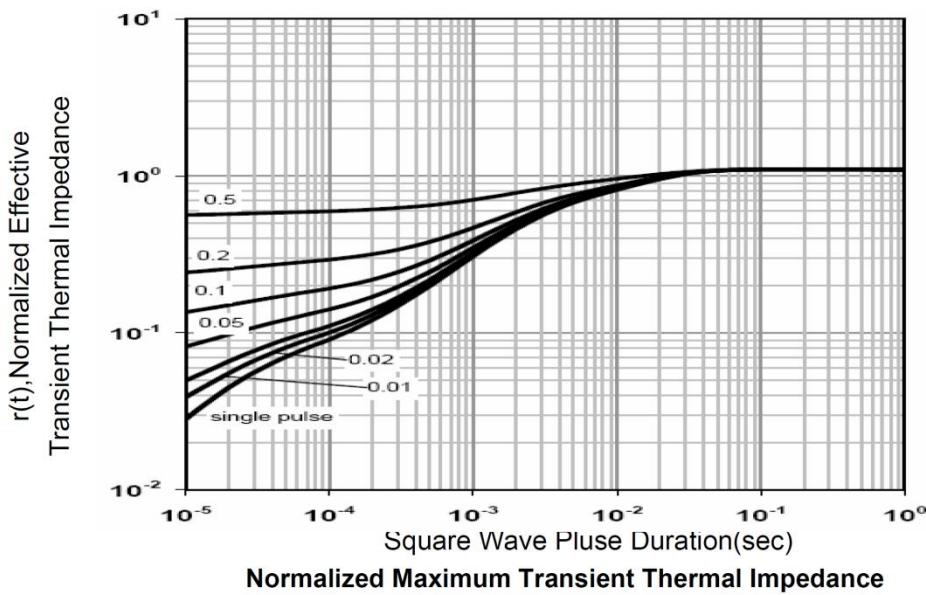
T<sub>J</sub>-Junction Temperature (°C)  
Power De-rating



V<sub>DS</sub> Drain-Source Voltage (V)  
Safe Operation Area



T<sub>J</sub>-Junction Temperature (°C)  
Current De-rating



Normalized Maximum Transient Thermal Impedance



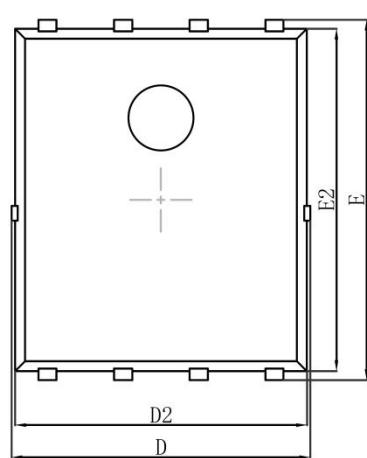
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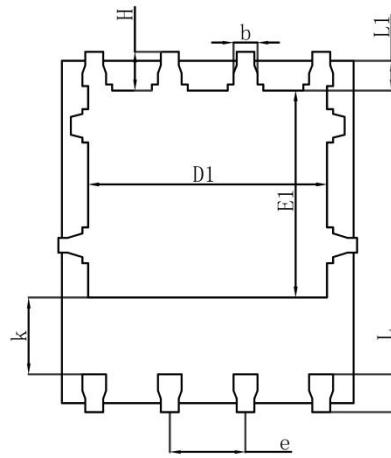
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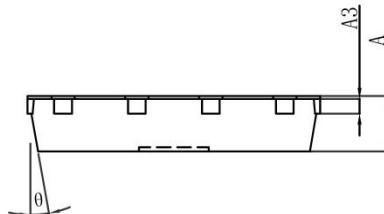
### PDFNW5X6-8L Package Information



Top View  
[顶视图]



Bottom View  
[背视图]



Side View  
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
$\theta$	10°	12°	10°	12°